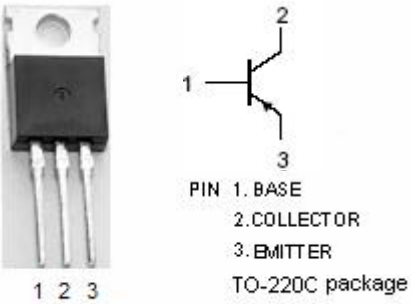
isc Silicon PNP Power Transistor — 2SA1006A

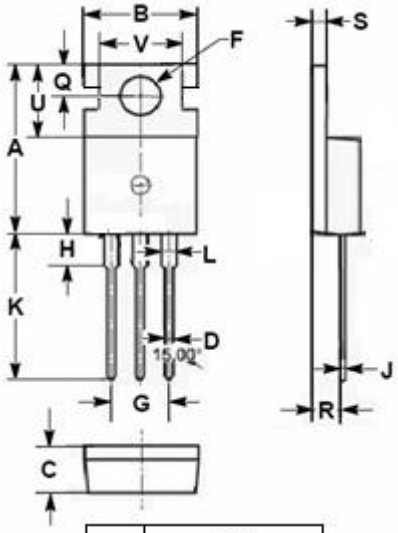
DESCRIPTION

- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -200V(Min)
- Wide Area of Safe Operation
- Complement to Type 2SC2336A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Adudio frequency power amplifier
- High frequency power amplifier



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-1.5	A
I_{CM}	Collector Current-Peak	-3.0	A
P_C	Collector Power Dissipation@ T_a=25℃	1.5	W
	Total Power Dissipation@ T_C=25℃	25	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -150V; I_E= 0			-1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -3.0V; I_C=0			-1.0	μA
h_{FE-1}	DC Current Gain	I_C= -5mA ; V_{CE}= -5V	30			
h_{FE-2}	DC Current Gain	I_C= -150mA ; V_{CE}= -5V	60		320	
f_T	Current-Gain—Bandwidth Product	I_C= -100mA ; V_{CE}= -10V		80		MHz
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= -10V;f= 1.0MHz		45		pF

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	100-200	160-320